

Model-No.: DFB-0785-100, DFB Diode Laser

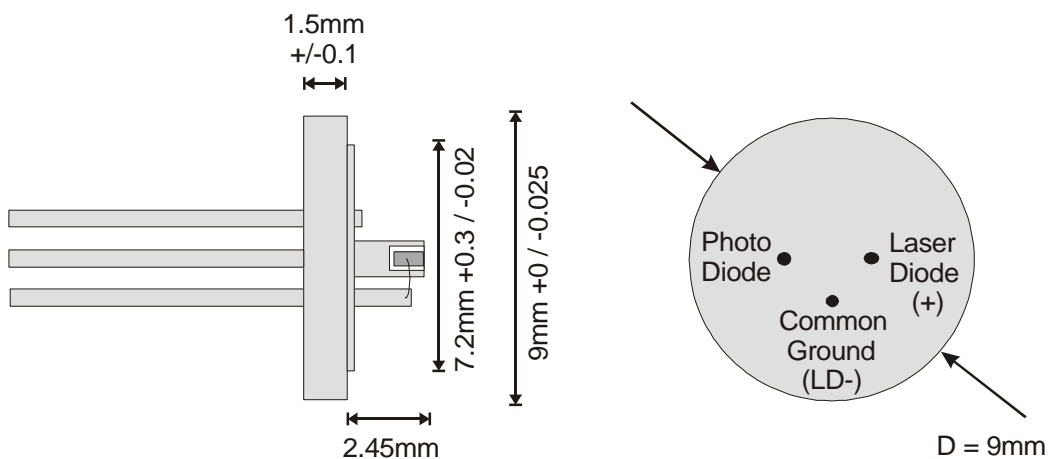


Description: The DFB-0785-100 is a high power MOVPE grown GaAsP/AlGaAs Distributed Feedback diode laser. The chips are mounted in 9mm TO-can. The diode laser operates spatially and longitudinally single mode. Manufacturer is Eagleyard Photonics.

Characteristics: The characteristics are measured at 25°C operation temperature.

Parameter	Symbol	Unit	Min.	typ.	max.
Center Wavelength	λ_c	nm	783	784	787
Spectral Width	$\Delta\lambda$	MHz		5	10
Temperature Coefficient	$\Delta T/\Delta\lambda$	m/K		0.04	
Output Power	P_{opt}	mW		100	120
Slope Efficiency	η	mW/mA	0.65	0.8	1.0
Threshold Current	I_{th}	mA			60
Operation Current @ 100mW	I_{op}	mA		150	200
Chip Length	L_c	μm		1500	
Emitter width	W_c	μm		4	
Beam Divergence (FWHM)	$\theta_{ }$	deg.		10	
Beam Divergence \perp (FWHM)	θ_{\perp}	deg.		30	
Polarization				TM	
Mode Structure			fundamental transverse mode		

Laser Mount: 9mm TO-can with monitor diode



Side View of the Laser Mount

Rear View of the Laser Mount

Document: <http://data.sacher-laser.com/dbr/DFB0785100.pdf>
 Note: Specification are subject to change without further notice

